

ABSTRACT OF THE DISCLOSURE

A method for manufacturing a semiconductor integrated circuit device includes the steps of forming an isolation trench in an isolation region of a semiconductor substrate, filling the isolation trench up to predetermined middle position in its depth direction with a first insulating film deposited by a coating method, filling a remaining depth portion of the isolation trench into which the first insulating film is filled with a second insulating film, then forming a plurality of patterns on the semiconductor substrate, filling a trench forming between the plurality of patterns up to predetermined middle position in a trench depth direction with a third insulating film deposited by a coating method, and filling a remaining portion of the trench into which the third insulating film is filled with a fourth insulating film that is more difficult to etch than the third insulating film. The method may also include the step of forming dummy patterns in a relatively large isolation region of isolation regions with relatively different planar dimensions before the first insulating film is deposited